N-Channel Enhancement Mode Power MOSFET

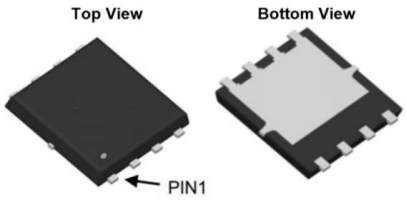
Description

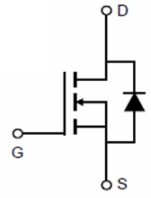
This Power MOSFET is produced using advanced TRENCH technology.
This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Features

- V_{DS}=30V , I_D=90A
- $R_{DS(ON)TYP}$ = 4.2mΩ @V_{GS} =10V
- $R_{DS(ON)TYP}$ = 5.6mΩ @V_{GS} =4.5V
- Very Low On-resistance RDS(ON)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

PDFN5*6-8L





Schematic diagram

Applications

- PWM Application
- Load Switch
- Power Management

100% UIS TESTED!

100% ΔVds TESTED!

RoHS

Package Marking and Ordering Information

Device Marking	Package	Packing	Reel (pcs)
SL90N03R	PDFN5*6	Reel	5000

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25℃	I_D	90	A
	T_C=100℃		58	
Pulsed Drain Current(T_C=25℃,T_p Limited By T_{jmax}) (note1)		I_{DM}	360	A
Maximum Power Dissipation(T_C=25℃)		P_D	90	W
Avalanche energy , single Pulse(L=0.5mH) (note2)		E_{AS}	90	mJ
Operating Junction And Storage Temperature		T_j,T_{stg}	-55 To 150	℃
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		T_L	300	℃

Thermal Resistance

Parameter	Symbol	Max	Unit
Junction-to-Case	$R_{\theta JC}$	1.67	℃/W

Note:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J =25℃, V_{DD} =15V, V_G =10V, R_G =25Ω, L=0.5mH, I_{AS} =19A
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%

Electrical Characteristic (TC=25℃unless otherwise noted)

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Off Characteristic						
Drain-source breakdown voltage	BV_{DSS}	30	-	-	V	V_{GS}=0V, I_D=250μA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=30V, V_{GS}=0V
		-	-	10	μA	V_{DS}=24V, TC =125℃
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V, V_{DS}=0V
On Characteristics						
Gate threshold voltage	$V_{GS(th)}$	1.0	1.5	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Drain-source on-state resistance	$R_{DS(on)}$	-	4.2	5.5	mΩ	V_{GS}=10V, I_D=30A
		-	5.6	7.3	mΩ	V_{GS}=4.5V, I_D=30A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	1950	-	PF	V_{GS}=0V, V_{DS}=15V, f=1.0MHz
Output Capacitance	C_{oss}	-	320	-		
Reverse Transfer Capacitance	C_{rss}	-	240	-		
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	-	13	-	nS	V_{DS}=15V, V_{GS}=10V, R_G=25Ω, I_D=30A
Turn-on Rise time	t_r	-	36	-		
Turn-off delay time	$t_{d(off)}$	-	43			
Turn-off Fall time	t_f	-	16	-		
Gate Total Charge	Q_G	-	42	-	nC	V_{GS}=10V, V_{DS}=15V, I_D=30A
Gate-Source Charge	Q_{gS}	-	4	-		
Gate-Drain Charge	Q_{gd}	-	14	-		
Drain-Source Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	-	-	1.2	V	V_{GS}=0V, I_{SD}=30A, T_J = 25℃
Body Diode Forward Current	Is	-	-	90	A	-
Body Diode Reverse Recovery Time	T_{rr}	-	16	-	ns	TJ=25℃, I_{SD}=20A, V_{GS}=0V, d_i/d_t =100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	5	-	nC	

N- Channel Typical Characteristics

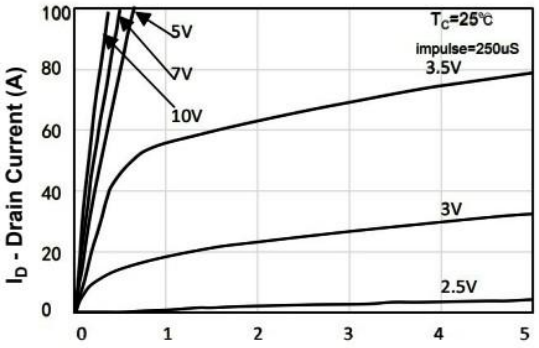


Figure 1. On-Region Characteristics

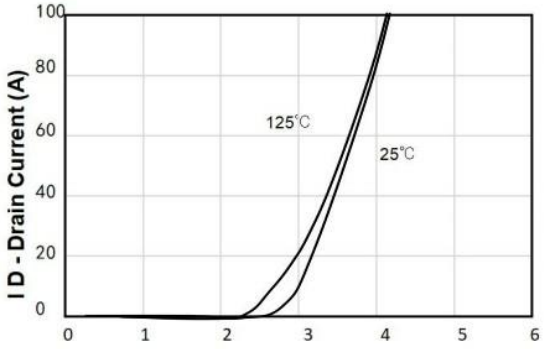


Figure 2. Transfer Characteristics

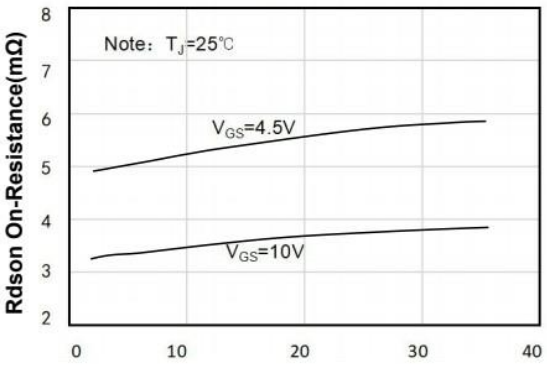


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

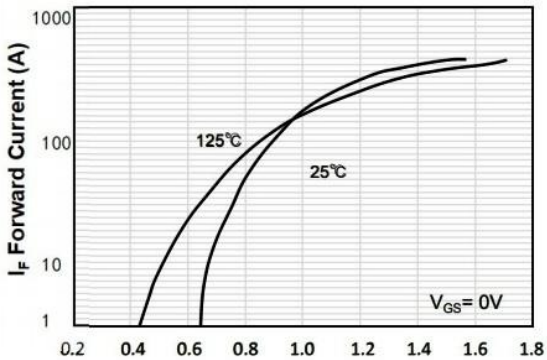


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

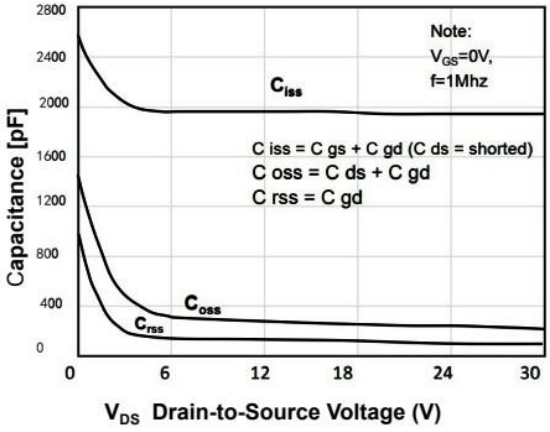


Figure 5. Capacitance Characteristics

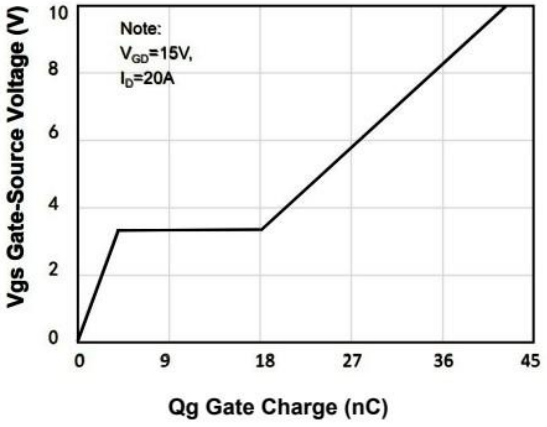


Figure 6. Gate Charge Characteristics

N- Channel Typical Characteristics (Continued)

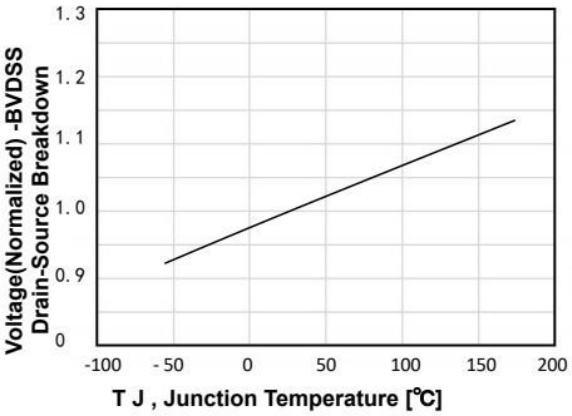


Figure 7. Breakdown Voltage Variation vs Temperature

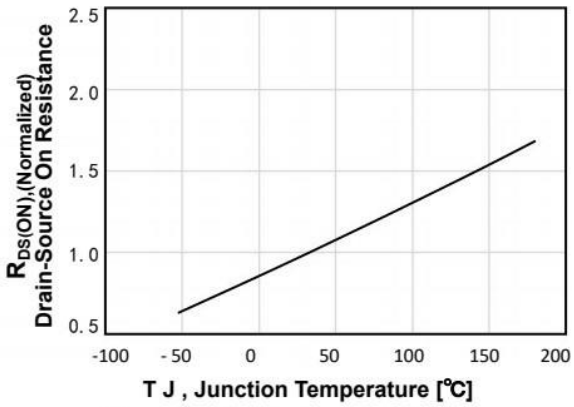


Figure 8. On-Resistance Variation vs Temperature

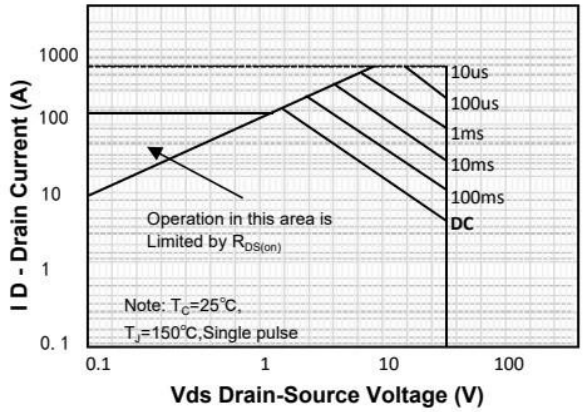


Figure 9. Maximum Safe Operating Area

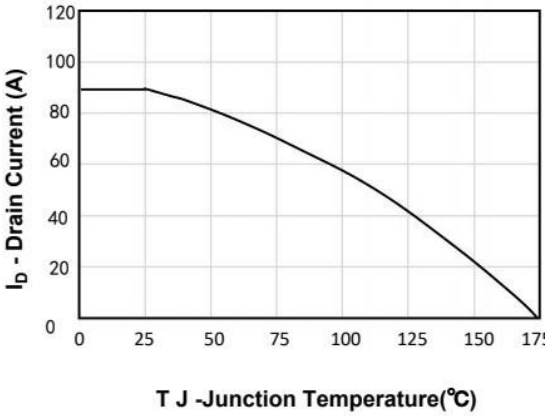


Figure 10. Maximum PContinuous Drain Currentvs Case Temperature

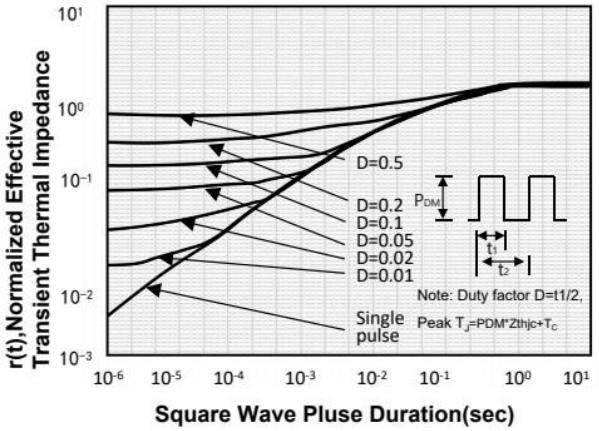
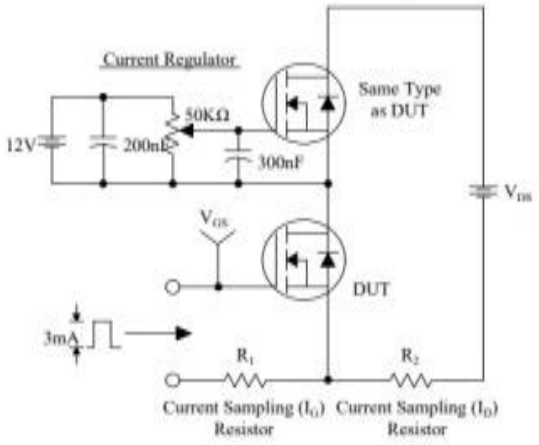
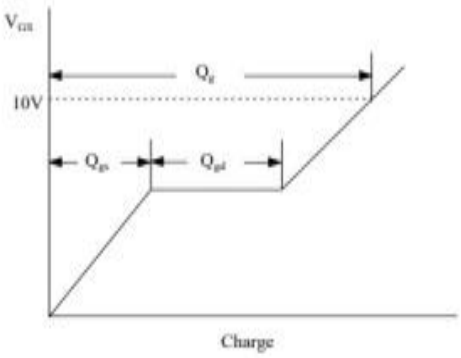


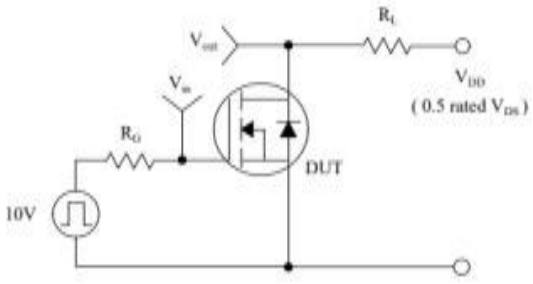
Figure 11. Transient Thermal Response Curve

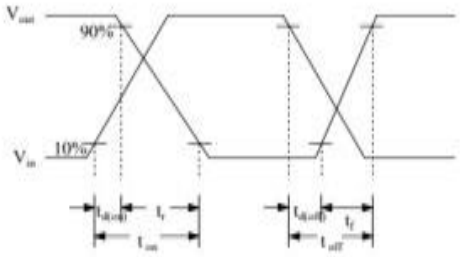
Gate Charge Test Circuit & Waveform



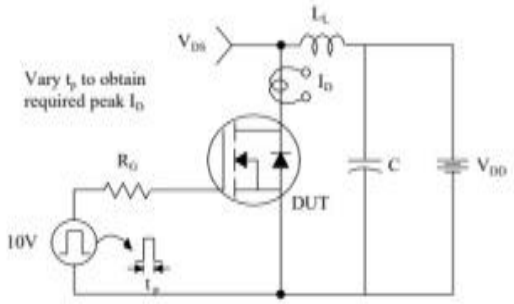


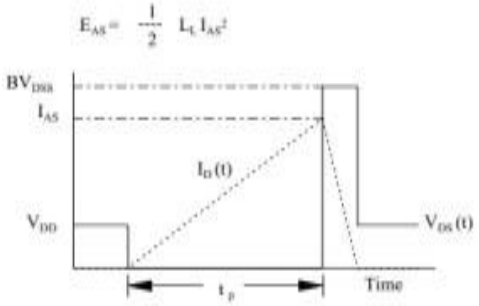
Resistive Switching Test Circuit & Waveforms



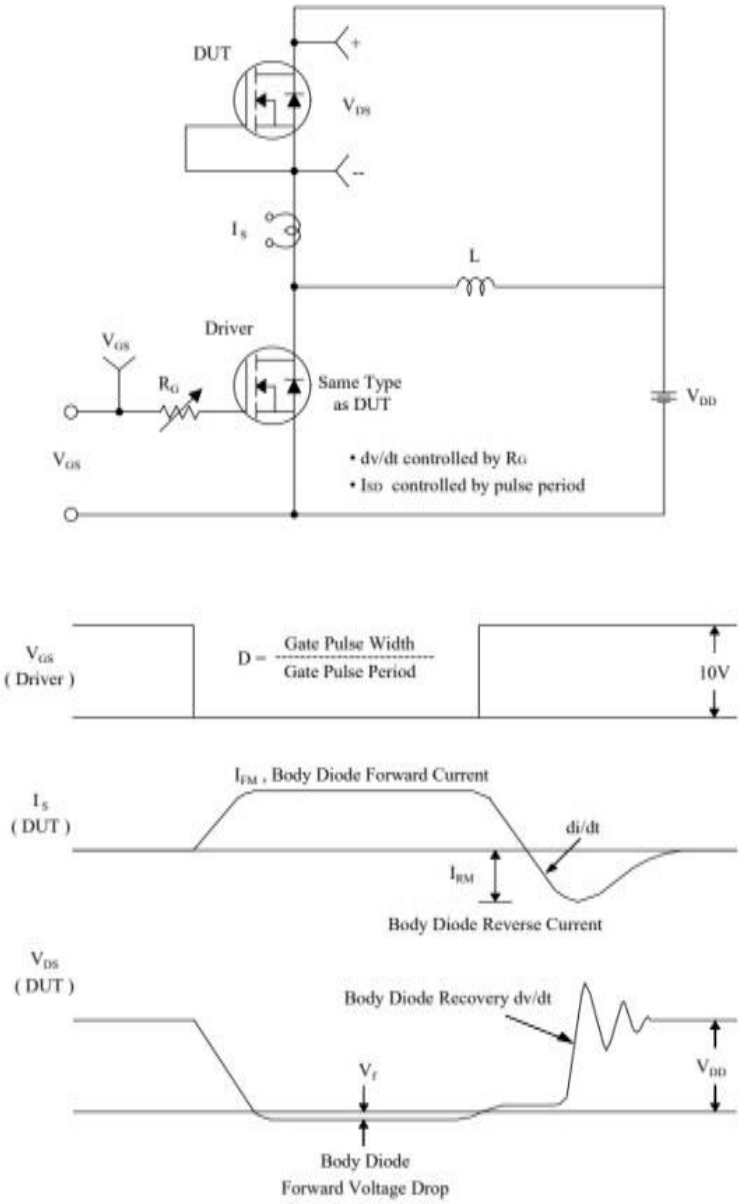


Unclamped Inductive Switching Test Circuit & Waveforms



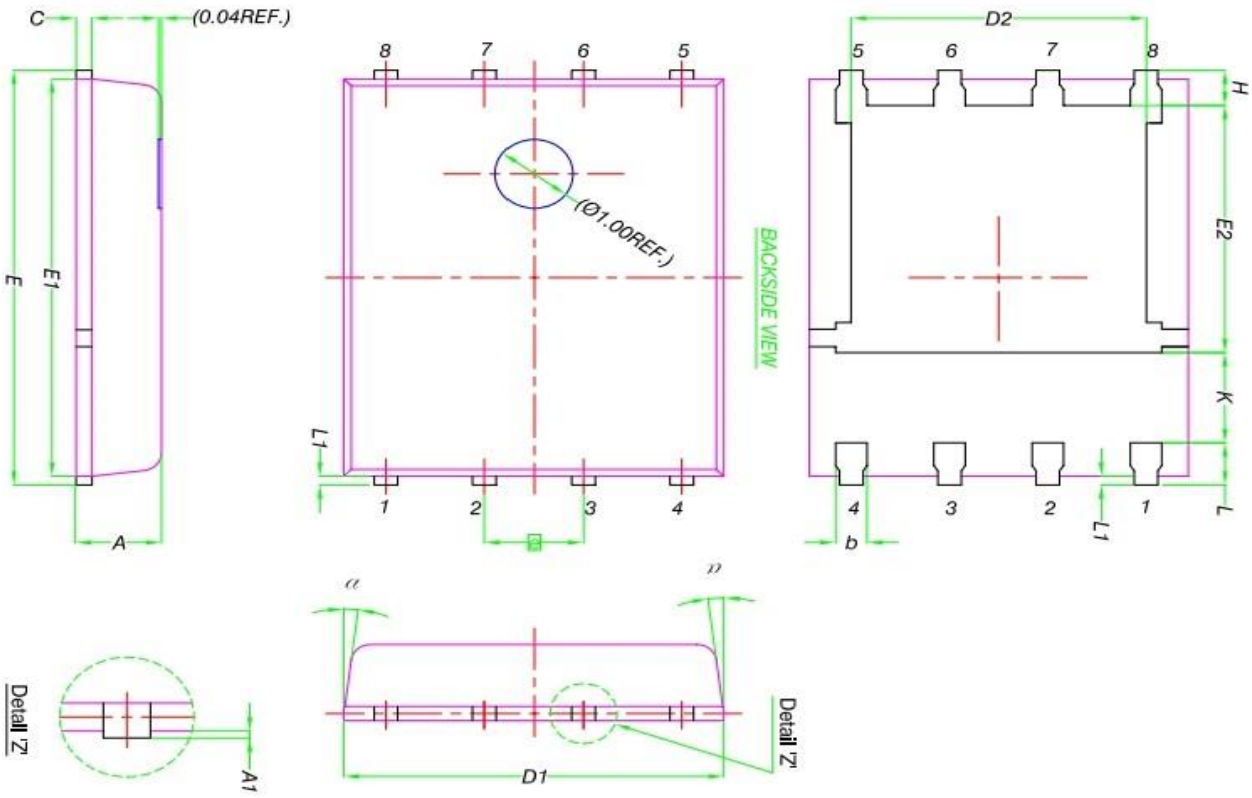


Peak Diode Recovery dv/dt Test Circuit & Waveforms

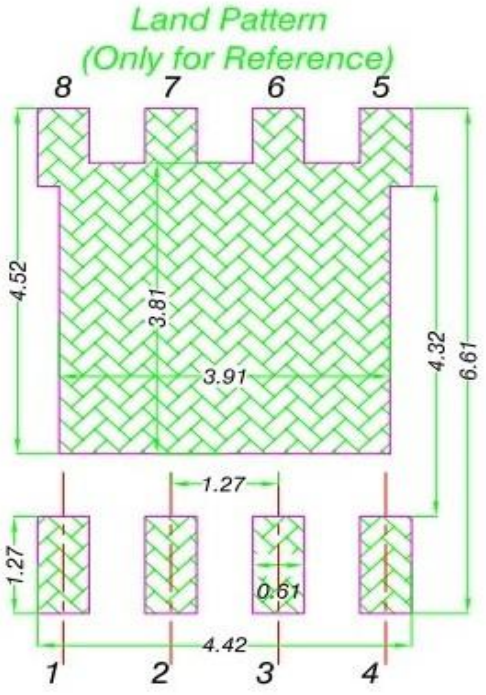


Package Information

PDFN5*6-8L



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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